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STMicroelectronics 2STR2215

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Low voltage fast-switching PNP power transistor

Features

- Very low collector-emitter saturation voltage
- High current gain characteristic
- Fast switching speed
- Miniature SOT-23 plastic package for surface mounting circuits

Applications

- LED
- Battery charger
- Motor and relay driver
- Voltage regulation

Description

The 2STR2215 is a PNP transistor manufactured using new "PB-HCD" (power bipolar high current density) technology. The resulting transistor shows exceptional high gath performances coupled with very low saturation voltage. The complementar (NPN) is the 2STR1215.



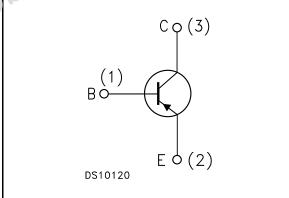


Table 1.Device summary

Order code	Marking	Package	Packaging
2STR2215	215	SOT-23	Tape and reel

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Electrical ratings

2STR2215

Electrical ratings 1

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-base voltage (I _E = 0)	-15	V
V _{CEO}	Collector-emitter voltage (I _B = 0)	-15	V
V _{EBO}	Emitter-base voltage (I _C = 0)	-5	V
Ι _C	Collector current	-1.5	Α
I _{CM}	Collector peak current (t _P < 5 ms)	-3	A
P _{tot}	Total dissipation at T _{amb} = 25 °C	0.5	W
T _{stg}	Storage temperature	- 35 '0 150	°C
TJ	Max. operating junction temperature	150	°C
	201		
Table 3.	Thermal data		
		No.1	

Table 3. Thermal data

Symbol	Parameter	Value	Unit	
$R_{thj-amb}^{(1)}$	Thermal resistance junction-amb	max	250	°C/W

Lite productions 1. Device mounted on PCB area of 1cm²



2 Electrical characteristics

 $(T_{case} = 25 \ ^{\circ}C \text{ unless otherwise specified})$

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{СВО}	Collector cut-off current (I _E =0)	V _{CB} = -15 V			-0.1	μA
I _{EBO}	Emitter cut-off current (I _C =0)	V _{EB} = -4 V			-0.1	μA
V _{(BR)CBO}	Collector-base breakdown voltage (I _E = 0)	I _C = -100 μΑ	-15	40		v
V _{(BR)CEO} ⁽¹⁾	Collector-emitter breakdown voltage (I _B = 0)	I _C = -10 mA	-\5			V
V _{(BR)EBO}	Emitter-base breakdown voltage ($I_{\rm C} = 0$)	l _E = -100 μA	-5			V
V _{CE(sat)} ⁽¹⁾	Collector-emitter saturation voltage	$I_{C} = -100 \text{ mA}$ $I_{B} = -1 \text{ mA}$ $I_{C} = -1 \text{ A}$ $I_{B} = -100 \text{ mA}$ $I_{C} = -2 \text{ A}$ $I_{B} = -200 \text{ mA}$		-0.25 -0.40	-0.15 -0.50 -0.85	> > >
V _{BE(sat)} ⁽¹⁾	Base-emitter saturation voltage	I _C = -1 A I _B = -100 mA		-0.90	-1.25	V
h _{FE} (1)	DC current gain	$\begin{array}{ll} I_{C} = -50 \text{ mA} & V_{CE} = -2 \text{ V} \\ I_{C} = -500 \text{ mA} & V_{CE} = -2 \text{ V} \\ I_{C} = -1 \text{ A} & V_{CE} = -2 \text{ V} \\ I_{C} = -2 \text{ A} & V_{CE} = -2 \text{ V} \end{array}$	200 200 130 80	280	560	
C _{CBO}	Collector-base capacitance (I _E = 0)	V _{CB} = -10 V f = 1 MHz		20		pF
t _{on} t _{off}	Resistive load Turn-on time Turn-off time	$I_{C} = -1.5 \text{ A}$ $V_{CC} = -10 \text{ V}$ $I_{B1} = -I_{B2} = -150 \text{ mA}$		60 220		ns ns

1. Pulsed duration = 300 μ s, duty cycle \leq 1.5%





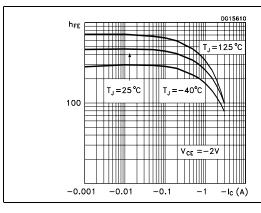
Figure 3.

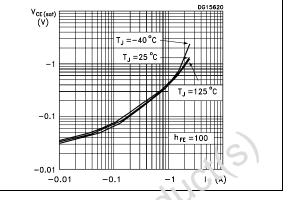
Electrical characteristics

2STR2215

2.1 Electrical characteristics (curves)

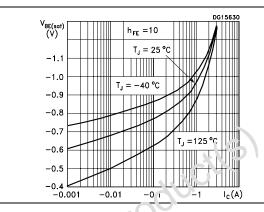
Figure 2. DC current gain





Collector-emitter saturation voltage

Figure 4. Base-emitter saturation voltage





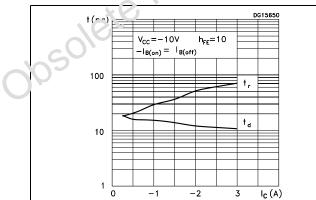


Figure 5. Resistive load switching time

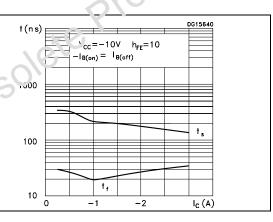
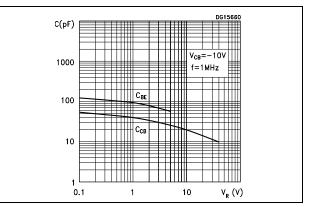


Figure 7. Capacitance

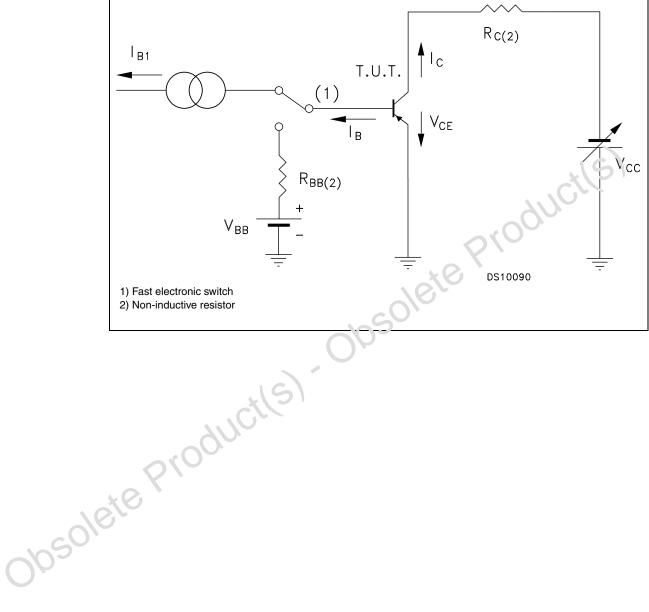


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2.2 Test circuit







Package mechanical data

2STR2215

3 Package mechanical data

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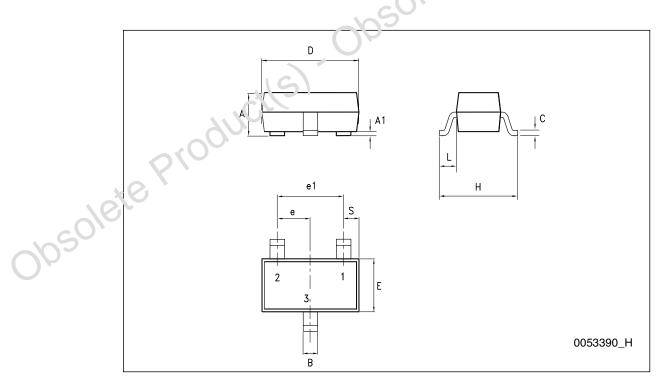




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Package mechanical data

	SOT-23 mechanical data				
DIM.		mm.			
DIM.	min.	typ	max.		
А	0.89		1.4		
A1	0		0.1		
В	0.3		0.51		
С	0.085		0.18		
D	2.75		3.04		
е	0.85		1.05		
e1	1.7		21		
E	1.2		1.6		
Н	2.1	0	2.75		
L		0.6			
S	0.35	161	0.65		





Revision history

2STR2215

4 Revision history

Table 5. Document revision history

Date	Revision	Changes
09-Feb-2006	1	Initial release.
20-Jul-2006	2	New template.
08-Sep-2008	3	Updated the SOT-23 mechanical data.
08-Jan-2009	4	Updated <i>Figure 1: Internal schematic diagram</i> Updated statement ECOPACK [®]
etepro	ductl	Updated statement ECOPACK®





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